



HFZT

RB521S-30

Schottky Barrier Diode

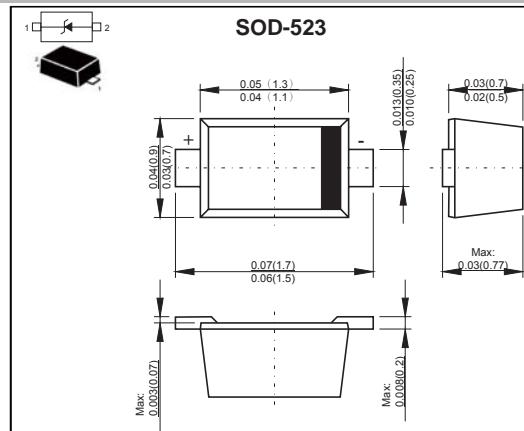
VOLTAGE RANGE: 30V PEAK PULSE POWER:150mW

FEATURE

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

MECHANICAL DATA

- Case: SOD-523 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

Parameter	Symbol	Limit	Unit
DC reverse voltage	VR	30	V
Mean rectifying current	IO	200	mA
Non-repetitive Peak forward surge current @ t=8.3ms	I _{FSM}	1	A
Power dissipation	PD	150	mW
Thermal Resistance Junction to Ambient	R _θ JA	667	°C/W
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+150	°C

Electrical Specification (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	VF1			0.35	V	F=10mA
	VF2			0.5	V	F=200mA
Reverse current	I _R			30	μA	VR=10V

MARKING: C



RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

